

D4SB80

PRV : 800 Volts
Io : 4.0 Amperes

FEATURES :

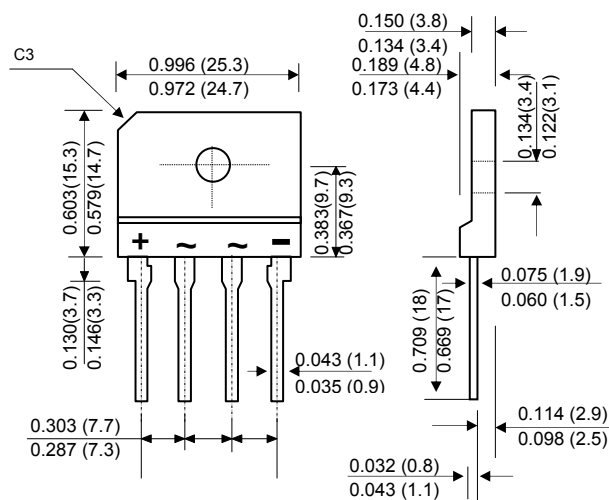
- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : Reliable low cost construction utilizing molded plastic technique
- * Epoxy : UL94V-O rate flame retardant
- * Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Polarity symbols marked on case
- * Mounting position : Any
- * Weight : 4.28 grams

SILICON BRIDGE RECTIFIER

RBV4



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (If not specified Tc = 25 °C)

RATING		SYMBOL	VALUE	UNIT
Maximum Reverse Voltage		V_{RM}	800	V
Maximum Average Rectified Forward Current (50 Hz sine wave, R-load)	With heatsink Tc = 108 °C	$I_{F(AV)}$	4.0	A
	Without heatsink Ta = 25 °C		2.3	
Maximum Peak Surge Forward Current, 50Hz sine wave, Non-repetitive 1 cycle peak value, Tj = 25 °C		I_{FSM}	150	A
Maximum Forward Voltage at $I_F = 2.0 A$ **		V_F	0.95	V
Maximum Reverse Current at $V_R = V_{RM}$ **		I_R	10	μA
Thermal Resistance, Junction to Case (With heatsink)		$R_{\theta JC}$	5.5	°C/W
Thermal Resistance, Junction to Lead (Without heatsink)		$R_{\theta JL}$	6.0	°C/W
Thermal Resistance, Junction to Ambient (Without heatsink)		$R_{\theta JA}$	30	°C/W
Operating Junction Temperature Range		T_J	150	°C
Storage Temperature Range		T_{STG}	- 40 to + 150	°C

** Pulse measurement, Rating of per diode.

RATING AND CHARACTERISTIC CURVES (D4SB80)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

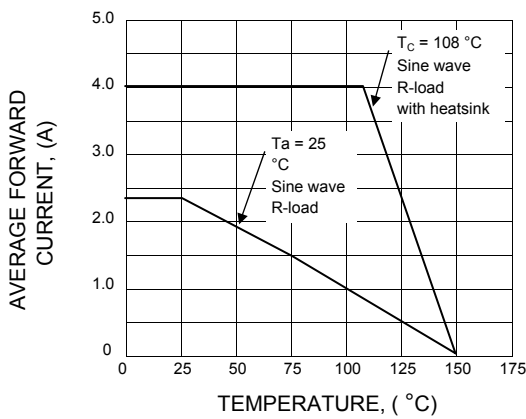


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

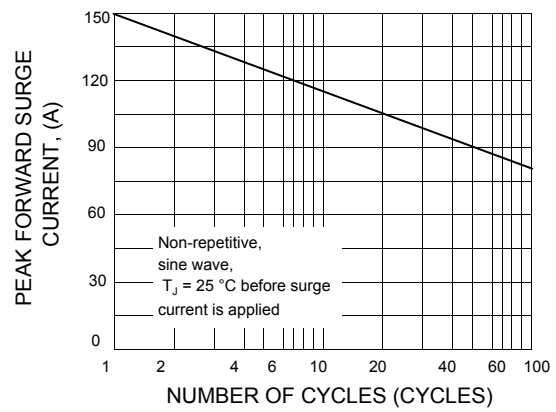


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

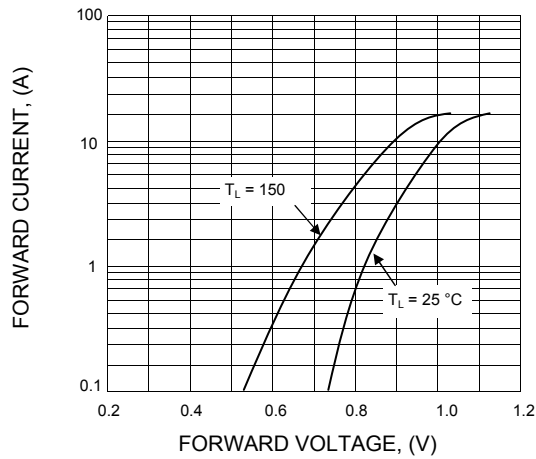


FIG.4 - FORWARD POWER DISSIPATION

